

Minimum Detectable Signal (MDS)

- Minimum Detectable Signal (MDS): Input signal level when the signal-to-noise ratio (SNR) is equal to unity

Ω Sensed Signal

$\Omega_{min} = \frac{N_{on}}{A}$

Scale factor A

Output v_o

Includes desired output plus noise

- The sensor scale factor is governed by the sensor type
- The effect of noise is best determined via analysis of the equivalent circuit for the system

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Move Noise Sources to a Common Point

- Move noise sources so that all sum at the input to the amplifier circuit (i.e., at the output of the sense element)
- Then, can compare the output of the sensed signal directly to the noise at this node to get the MDS

can do the analysis only up to this node

Output

Includes desired output plus noise

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Example: TransR Amplifier Noise

Input-referred current noise:
Open inputs; equate output voltage noise.

Case I:
 $N_{oi1} = i_{ia} R_f$
 $N_{oi2} = i_f R_f$
 $N_{oi3} = N_{ia}$
 Move N_{ia} through R_{in} to N_{ia}
 This is unity gain!

Case II:
 $N_{oi2} = i_{ia} R_f^2 + i_f^2 R_f^2 + N_{ia}^2$
 $N_{oi1} = i_{ia} R_f^2$
 $N_{oi3} = N_{ia}^2$
 $N_{eq} = i_{ia}^2 + i_f^2 + \frac{N_{ia}^2}{R_f^2}$

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Example: TransR Amplifier Noise (cont)

Input-referred voltage noise:
Short inputs; equate output voltage noise.

Case I:
 $N_{oi2} = N_{ia}^2 a^2$
 (Both i_{ia}^2 & i_f^2 are shorted out.)

Case II:
 $N_{oi2} = N_{eq}^2 a^2$
 $N_{eq} = N_{ia}^2$

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Example: TransR Amplifier Noise (cont)

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- To summarize, for a transresistance amplifier, the equivalent input-referred current and voltage noise generators are given by:

$$\overline{i_{eq}^2} = \overline{i_{ia}^2} + \overline{i_f^2} + \frac{\overline{v_{ia}^2}}{R_f^2}$$

$$\overline{v_{eq}^2} = \overline{v_{ia}^2}$$

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Back to Gyro Noise & MDS

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Example: Gyro MDS Calculation

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$\vec{F}_c = m\vec{a}_c = m \cdot (2\vec{\dot{x}}_d \times \vec{\Omega})$

- The gyro sense presents a large effective source impedance
 - Currents are the important variable; voltages are "opened" out
 - Must compare i_o with the total current noise i_{eqTOT} going into the amplifier circuit

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Example: Gyro MDS Calculation (cont)

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$\vec{F}_c = m\vec{a}_c = m \cdot (2\vec{\dot{x}}_d \times \vec{\Omega})$

- First, find the rotation to i_o transfer function:

$$\dot{x}_s = \frac{\omega_s Q}{k_s} \Theta_s(j\omega_d) F_s = \frac{\omega_s Q}{k_s} \cdot 2\omega_d \kappa_d \Omega m \cdot \Theta(j\omega_d)$$

$$[F_s = F_c = 2\omega_d \kappa_d \Omega m]$$

$$\dot{x}_s = 2 \frac{\omega_d}{\omega_s} Q \kappa_d \Theta(j\omega_d) \cdot \Omega$$

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Example: Gyro MDS Calculation (cont)

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$$i_o = \eta_e \dot{x}_s = 2 \frac{\omega_d}{\omega_s} Q \kappa_d \eta_e \Theta(j\omega_d) \cdot \Omega \rightarrow i_o = A \Omega$$

$A \triangleq \text{scale factor}$
Where $A = 2 \frac{\omega_d}{\omega_s} Q \kappa_d \eta_e \Theta(j\omega_d)$

When $\Omega = \Omega_{\min} \triangleq \text{MDS}$, $i_o = i_{eqTOT}$ ← input-referred noise current entering the sense amplifier → in pA/√Hz

$$\therefore i_{eqTOT} = A \Omega_{\min} \rightarrow \Omega_{\min} = \frac{i_{eqTOT}}{A} \left(\frac{3600s}{hr} \right) \left(\frac{180^\circ}{\pi} \right) \left[\left(\frac{\circ}{hr} \right) / \sqrt{Hz} \right]$$

$$\text{Angle Random Walk} = \text{ARW} = \frac{1}{60} \Omega_{\min} \left[\frac{\circ}{\sqrt{hr}} \right]$$

↙ Earlier to determine directional error as a function of elapsed time.

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Example: Gyro MDS Calculation (cont)

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$$\vec{F}_c = m \vec{a}_c = m \cdot (2\vec{x}_d \times \vec{\Omega})$$

• Now, find the i_{eqTOT} entering the amplifier input:

$$i_{eqTOT}^2 = i_s^2 + i_{eq}^2 \rightarrow i_{eqTOT}^2 = i_s^2 + i_f^2 + i_a^2 + \frac{N_{ia}^2}{R_f^2}$$

$\frac{N_{ia}^2}{R_f^2} = \frac{4kTR_x}{\Delta f}$
↙ Brownian motion noise of the sense element → determined entirely by the noise in $r_x \rightarrow f_{rx}^2$
↙ easiest to convert to an all electrical equiv. ckt.

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Example: Gyro MDS Calculation (cont)

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where $L_x = \frac{R_x}{\eta_e}$, $C_x = \eta_e C_x$, $R_x = \frac{r_x}{\eta_e}$

$$\therefore i_s^2 = N_{R_x} \left(\frac{1}{R_x} \right) \Theta(j\omega_d) \rightarrow \frac{i_s^2}{\Delta f} = 4kTR_x \left(\frac{1}{R_x} \right) \Theta(j\omega_d)^2$$

$$\Rightarrow \frac{i_s^2}{\Delta f} = \frac{4kT}{R_x} \Theta(j\omega_d)^2$$

$$\frac{i_{eqTOT}^2}{\Delta f} = \frac{4kT}{R_x} \Theta(j\omega_d)^2 + \frac{4kT}{R_f} + \frac{i_a^2}{\Delta f} + \frac{N_{ia}^2}{\Delta f} \left(\frac{1}{R_f} \right)$$

Learn to get these from EE240.
↙ or just get them from a data sheet ...

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LF356 Op Amp Data Sheet

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LF155/LF156/LF256/LF257/LF355/LF356/LF357

JFET Input Operational Amplifiers

General Description

These are the first monolithic JFET input operational amplifiers to incorporate well matched, high voltage JFETs on the same chip with standard bipolar transistors (BI-FET™ Technology). These amplifiers feature low input bias and offset currents/low offset voltage and offset voltage drift, coupled with offset adjust which does not degrade drift or common-mode rejection. The devices are also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner.

Features

- Replace expensive hybrid and module FET op amps
- Rugged JFETs allow blow-out free handling compared with MOSFET input devices
- Excellent for low noise applications using either high or low source impedance — very low 1/f corner
- Offset adjust does not degrade drift or common-mode rejection as in most monolithic amplifiers
- New output stage allows use of large capacitive loads (5,000 pF) without stability problems
- Internal compensation and large differential input voltage capability

Applications

- Precision high speed integrators
- Fast D/A and A/D converters
- High impedance buffers
- Wideband, low noise, low drift amplifiers

Common Features

- Logarithmic amplifiers
- Photocell amplifiers
- Sample and Hold circuits
- Low input bias current: 30pA
- Low Input Offset Current: 3pA
- High input impedance: $10^{10} \Omega$
- Low input noise current: $0.01 \text{ pA}/\sqrt{Hz}$
- High common-mode rejection ratio: 100 dB
- Large dc voltage gain: 106 dB

Uncommon Features

	LF155/ LF355	LF156/ LF256/ LF356	LF257/ LF357 (A _v =5)	Units
Extremely fast settling time to 0.01%	4	1.5	1.5	μs
Fast slew rate	5	12	50	V/μs
Wide gain bandwidth	2.5	5	20	MHz
Low input noise voltage	20	12	12	nV/√Hz

$\frac{i_a^2}{\Delta f} = 0.01 \text{ pA}/\sqrt{Hz}$

$\frac{N_{ia}^2}{\Delta f} = 12 \text{ nV}/\sqrt{Hz}$

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Example ARW Calculation

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Example Design:

- Sensor Element:**
 - $m = (100\mu\text{m})(100\mu\text{m})(20\mu\text{m})(2300\text{kg/m}^3) = 4.6 \times 10^{-10}\text{kg}$
 - $\omega_s = 2\pi(15\text{kHz})$
 - $\omega_d = 2\pi(10\text{kHz})$
 - $k_s = \omega_s^2 m = 4.09\text{ N/m}$
 - $x_d = 20\ \mu\text{m}$
 - $Q_s = 50,000$
 - $V_p = 5\text{V}$
 - $h = 20\ \mu\text{m}$
 - $d = 1\ \mu\text{m}$
- Sensing Circuitry:**
 - $R_f = 100\text{k}\Omega$
 - $i_{ia} = 0.01\ \text{pA}/\sqrt{\text{Hz}}$
 - $v_{ia} = 12\ \text{nV}/\sqrt{\text{Hz}}$

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Example ARW Calculation (cont)

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Get rotation rate to output current scale factor:

$$A = 2 \frac{\omega_d}{\omega_s} Q_s x_d \eta_e |\Theta(j\omega_d)| = 2 \left(\frac{10\text{k}}{15\text{k}} \right) (50\text{k}) (20\mu) (5) (2000\epsilon_0) (0.000024) = 2.83 \times 10^{-12} \text{C}$$

$$|\Theta(j\omega_d)| = \frac{(j\omega_d)(\omega_s/\omega_s)}{-\omega_d^2 + \frac{j\omega_d\omega_s}{Q_s} + \omega_s^2} = \frac{j(10\text{k})(15\text{k})/(50\text{k})}{(15\text{k})^2 - (10\text{k})^2 + \frac{j(10\text{k})(15\text{k})}{50\text{k}}} = \frac{j(3\text{k})}{1.25 \times 10^8 + j(3\text{k})}$$

$$\Rightarrow |\Theta(j\omega_d)| = \frac{3\text{k}}{\sqrt{(1.25 \times 10^8)^2 + (3\text{k})^2}} = 0.000024 \quad 8.854 \times 10^{-12} \text{F/m}$$

$$\frac{\partial C}{\partial x} = \frac{C_0}{d} = \frac{\epsilon_0 h \omega_p}{d} = \frac{\epsilon_0 (20\mu)(100\mu)}{(1\mu)^2} = 2000\epsilon_0 \rightarrow \eta_e = V_p \frac{\partial C}{\partial x} = 5(2000\epsilon_0) \quad 8.854 \times 10^{-12} \text{F/m}$$

Assume electrode covers the whole sidewall.

Then, get noise:

$$\frac{i_{eqTOT}^2}{\Delta f} = \frac{4KT}{R_x} |\Theta(j\omega_d)|^2 + \frac{4KT}{R_f} + \frac{i_{ia}^2}{\Delta f} + \frac{v_{ia}^2}{\Delta f} \left(\frac{1}{R_f} \right)$$

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Example ARW Calculation (cont)

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$$R_x = \frac{\omega_s m}{Q_s \eta_e^2} = \frac{2\pi(15\text{k})(4.6 \times 10^{-10})}{(50\text{k})(8.85 \times 10^{-12})^2} = 110.6\text{ k}\Omega$$

$$\frac{i_{eqTOT}^2}{\Delta f} = \frac{(1.66 \times 10^{-29})}{(110.6\text{k})} (0.000024)^2 + \frac{(1.66 \times 10^{-29})}{1\text{M}} + (0.01\text{p})^2 + \frac{(12\text{n})^2}{(1\text{M})^2}$$

$8.64 \times 10^{-35} \text{A}^2/\text{Hz}$ $1.66 \times 10^{-26} \text{A}^2/\text{Hz}$ $1 \times 10^{-28} \text{A}^2/\text{Hz}$ $1.44 \times 10^{-28} \text{A}^2/\text{Hz}$

sensor element noise insignificant Noise from R_f dominates!

$$\therefore \frac{i_{eqTOT}^2}{\Delta f} = 1.68 \times 10^{-26} \text{A}^2/\text{Hz} \rightarrow i_{eqTOT} = \sqrt{\frac{i_{eqTOT}^2}{\Delta f}} = 1.30 \times 10^{-13} \text{A}/\sqrt{\text{Hz}}$$

$$\therefore \Omega_{min} = \frac{i_{eqTOT}}{A} \left(\frac{3600\text{s}}{\text{hr}} \right) \left(\frac{180^\circ}{\pi} \right) = \frac{1.30 \times 10^{-13}}{2.83 \times 10^{-7}} (3600) \left(\frac{180^\circ}{\pi} \right) = 9448 (\%/hr)/\sqrt{\text{Hz}}$$

And finally:

$$ARW = \frac{1}{60} \Omega_{min} = \frac{1}{60} (9448) = 157 \%/hr = ARW \Rightarrow \text{Almost turned around in 1 hour!}$$

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What if $\omega_d = \omega_s$?

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If $\omega_d = \omega_s = 15\text{kHz}$, then $|\Theta(j\omega_d)| = 1$ and

$$A = 2 \frac{\omega_d}{\omega_s} Q_s x_d \eta_e |\Theta(j\omega_d)| = 2 Q_s x_d \eta_e = 2(50\text{k})(20\mu)(5)(2000\epsilon_0) = 1.77 \times 10^{-7} \text{C}$$

$$\frac{i_{eqTOT}^2}{\Delta f} = \frac{(1.66 \times 10^{-29})}{(110.6\text{k})} (1)^2 + \frac{(1.66 \times 10^{-29})}{1\text{M}} + (0.01\text{p})^2 + \frac{(12\text{n})^2}{(1\text{M})^2}$$

$1.51 \times 10^{-25} \text{A}^2/\text{Hz}$ $1.66 \times 10^{-26} \text{A}^2/\text{Hz}$ $1 \times 10^{-28} \text{A}^2/\text{Hz}$ $1.44 \times 10^{-28} \text{A}^2/\text{Hz}$

Now, the sensor element dominates!

$$\therefore \frac{i_{eqTOT}^2}{\Delta f} = 1.67 \times 10^{-25} \text{A}^2/\text{Hz} \rightarrow i_{eqTOT} = \sqrt{\frac{i_{eqTOT}^2}{\Delta f}} = 4.08 \times 10^{-13} \text{A}/\sqrt{\text{Hz}}$$

$$\therefore \Omega_{min} = \frac{i_{eqTOT}}{A} \left(\frac{3600\text{s}}{\text{hr}} \right) \left(\frac{180^\circ}{\pi} \right) = \frac{4.08 \times 10^{-13}}{1.77 \times 10^{-7}} (3600) \left(\frac{180^\circ}{\pi} \right) = 0.476 (\%/hr)/\sqrt{\text{Hz}}$$

And finally:

$$ARW = \frac{1}{60} \Omega_{min} = \frac{1}{60} (0.476) = 0.0079 \%/hr = ARW \Rightarrow \text{Navigation grade!}$$

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